

**LISTING OF THE CLAIMS**

Claims 1-9 (Canceled).

Claim 10 (Currently Amended): A semiconductor component comprising;

at least one first vertical power component (5,6,9) extending from a front side to a back side of a silicon substrate (1); and

at least one lateral, active component (6) ~~and/or~~ and optionally at least one second vertical power component (10), between which at least one trench (2) filled with an insulation (4) is placed, said at least one trench (2) extending from said front side to said back side of said silicon substrate (1),

wherein said insulation (4) comprises at least partly one dielectric and wherein said at least one vertical power component (5,9) and said at least one lateral, active component (6) are designed approximately ring-shaped and/or disk-shaped and are arranged eccentrically or concentrically around a common point of reference on ~~a~~ said silicon substrate (1).

Claim 11 (Original): A semiconductor component according to claim 10, wherein said at least one power component (5,9) is an IGBT, a PMOS and/or a diode.

Claim 12 (Previously Presented): A semiconductor component according to claim 10, wherein said at least one power component (5,9) is suited for voltages of up to 1700 V.

Claim 13 (Previously Presented): A semiconductor component according to claim 10, wherein said insulation (4) is composed of a combination of insulating, semiconducting and/or conducting materials.

Claim 14 (Previously Presented): A semiconductor component according to claim 10, wherein said insulation (4) is composed of a combination of a dielectric and polysilicon.

Claim 15 (Previously Presented): A semiconductor component according to claim 10, wherein said first vertical power component (5,9) and/or said at least one lateral, active component (6) is completely encompassed by at least one filled trench (2) and/or said at least one second vertical power component (10).

Claim 16 (Previously Presented): A semiconductor component according to claim 10, wherein said at least one lateral, active component (6) is placed in a doped trough.

Claim 17 (Currently Amended): A semiconductor component according to claim 10, wherein a dielectric (13) is applied on ~~the~~ said back side of said substrate (1) ~~semiconductor component~~.

Claim 18 (Currently Amended): A semiconductor component according to claim 17, wherein said dielectric (13) is provided with openings through which said power components (5,9,10) are contactable.